Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S42	1	10/680,878	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/24 10:45
S44	5137	S43 and (ONO or (oxide near3 nitride near3 oxide))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/24 10:49
S43	104622	(nonvolatile (non adj volatile) flash) and programm$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/24 10:49
S7	1609	(source with ground) same (drain with (bias potential volt$3)) same (gate with (bias potential volt$3)) same (substrate with (bias potential volt$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/24 10:50
S47	165	S43 and S46	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/24 10:51
S46	165	S44 and S45	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/24 10:51
S45	577	(source with ground) same (drain with (bias potential volt$3)) same (gate with (bias potential volt$3)) same (substrate with (bias potential volt$3)) same (program$5 writ$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/24 10:51
S40	8	S35 and ((program$5 writ$3) adj2 line)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/24 12:41

S53	2	S52 and (localiz$3 near3 charg$3) same (nitride near3 layer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/24 12:42
S52	165	S48 and S51	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/24 12:42
S51	165	S49 and S50	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/24 12:42
S50	577	(source with ground) same (drain with (bias potential volt$3)) same (gate with (bias potential volt$3)) same (substrate with (bias potential volt$3)) same (program$5 writ$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/24 12:42
S49	5137	S48 and (ONO or (oxide near3 nitride near3 oxide))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/24 12:42
L19	390	365/185.27.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/24 13:20
L18	1613	365/185.18.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/24 13:20
L22	1814	(L18 or L19)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/24 13:21

L21	1354	365/185.29.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/24 13:21
L20	784	365/185.28.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/24 13:21
S48	104622	(nonvolatile (non adj volatile) flash) and programm$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/24 13:22
S2	3228	S1 and ONO	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/24 13:22
L25	178963	(nonvolatile (non adj volatile) flash) and (programm$3 or writ$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/24 13:22
L24	1814	L22 and L22	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/24 13:22
L23	236	L22 and L20	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/24 13:22
L29	98	L27 and L28	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/24 13:23

L28	473	L24 and L26	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/24 13:23
L27	98	L23 and L26	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/24 13:23
L26	8014	L25 and (ONO or (oxide near3 nitride near3 oxide))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/24 13:23